Davide Bisi

List of Publications by Year
in descending order

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18	1,014	12	15
papers	citations	h-index	g-index
		758635	996533

18	18	18	852
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Deep-Level Characterization in GaN HEMTs-Part I: Advantages and Limitations of Drain Current Transient Measurements. IEEE Transactions on Electron Devices, 2013, 60, 3166-3175.	1.6	324
2	Buffer Traps in Fe-Doped AlGaN/GaN HEMTs: Investigation of the Physical Properties Based on Pulsed and Transient Measurements. IEEE Transactions on Electron Devices, 2014, 61, 4070-4077.	1.6	139
3	Negative Bias-Induced Threshold Voltage Instability in GaN-on-Si Power HEMTs. IEEE Electron Device Letters, 2016, 37, 474-477.	2.2	102
4	Temperature-Dependent Dynamic <inline-formula> <tex-math notation="LaTeX">$R_{mathrm {mathrm{{scriptstyle ON}}}}$ </tex-math></inline-formula> in GaN-Based MIS-HEMTs: Role of Surface Traps and Buffer Leakage. IEEE Transactions on Electron Devices, 2015, 62, 782-787.	1.6	91
5	Kinetics of Buffer-Related R_{ON}-Increase in GaN-on-Silicon MIS-HEMTs. IEEE Electron Device Letters, 2014, 35, 1004-1006.	2.2	84
6	Trapping mechanisms in GaNâ€based MISâ€HEMTs grown on silicon substrate. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 1122-1129.	0.8	63
7	Trapping and reliability issues in GaN-based MIS HEMTs with partially recessed gate. Microelectronics Reliability, 2016, 58, 151-157.	0.9	38
8	Hot-Electron Degradation of AlGaN/GaN High-Electron Mobility Transistors During RF Operation: Correlation With GaN Buffer Design. IEEE Electron Device Letters, 2015, 36, 1011-1014.	2.2	28
9	Improved Dynamic R_{ON} of GaN Vertical Trench MOSFETs (OG-FETs) Using TMAH Wet Etch. IEEE Electron Device Letters, 2018, 39, 1030-1033.	2.2	25
10	Observation of Hot Electron and Impact Ionization in N-Polar GaN MIS-HEMTs. IEEE Electron Device Letters, 2018, 39, 1007-1010.	2.2	23
11	Reliability and failure physics of GaN HEMT, MIS-HEMT and p-gate HEMTs for power switching applications: Parasitic effects and degradation due to deep level effects and time-dependent breakdown phenomena. , 2015, , .		22
12	GaN-Based Power HEMTs: Parasitic, Reliability and High Field Issues. ECS Transactions, 2013, 58, 187-198.	0.3	17
13	Analysis of slow de-trapping phenomena after a positive gate bias on AlGaN/GaN MIS-HEMTs with in-situ Si3N4/Al2O3 bilayer gate dielectrics. Solid-State Electronics, 2015, 103, 127-130.	0.8	16
14	Observation of I_D-V_D Kink in N-Polar GaN MIS-HEMTs at Cryogenic Temperatures. IEEE Electron Device Letters, 2020, 41, 345-348.	2.2	15
15	Drain current transient and low-frequency dispersion characterizations in AlGaN/GaN HEMTs. International Journal of Microwave and Wireless Technologies, 2016, 8, 663-672.	1.5	13
16	Trap investigation under class AB operation in AlGaN/GaN HEMTs based on output-admittance frequency dispersion, pulsed and transient measurements. , 2015, , .		6
17	Reliability of power devices: Bias-induced threshold voltage instability and dielectric breakdown in GaN MIS-HEMTs. , 2016, , .		4
18	Impact of oxygen precursor flow on the forward bias behavior of MOCVD-Al2O3 dielectrics grown on GaN. Journal of Applied Physics, 2017, 122, 174101.	1.1	4